**Product data sheet** 

## 1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a leadless medium power DFN2020MD-6 (SOT1220) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

### 2. Features and benefits

- · Very fast switching
- Low threshold voltage
- Trench MOSFET technology
- Side wettable flanks for optical solder inspection
- · Exposed drain pad for excellent thermal conduction

## 3. Applications

- · Relay driver
- · High-speed line driver
- · Low-side load switch
- · Switching circuits

## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	40	V
V <sub>GS</sub>	gate-source voltage			-8	-	8	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 25 °C; t ≤ 5 s	[1]	-	-	11.5	Α
Static characte	Static characteristics						
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 8.1 \text{ A}; T_j = 25 \text{ °C}$		-	15	18	mΩ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.



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# 5. Pinning information

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	D	drain	15776	D I
2	D	drain		
3	G	gate	2 5	G (F)
4	S	source	3 8 4	s
5	D	drain	Transparent top view	017aaa253
6	D	drain	DFN2020MD-6 (SOT1220)	
7	D	drain		
8	S	source		

# 6. Ordering information

### **Table 3. Ordering information**

Type number	Package					
	Name	Description	Version			
PMPB14XN		plastic, leadless thermal enhanced ultra thin small outline package with side-wettable flanks (SWF); 6 terminals; 0.65 mm pitch; 2 mm x 2 mm x 0.65 mm body	SOT1220			

# 7. Marking

#### Table 4. Marking codes

Type number	Marking code
PMPB14XN	5D

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## 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	40	V
V <sub>GS</sub>	gate-source voltage			-8	8	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 25 °C; t ≤ 5 s	[1]	-	11.5	А
		V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	8.1	Α
		V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 100 °C	[1]	-	5.1	А
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \mu s$		-	33	А
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[1]	-	1.9	W
		T <sub>amb</sub> = 25 °C; t ≤ 5 s	[1]	-	3.8	W
		T <sub>sp</sub> = 25 °C		-	12.5	W
Tj	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
Source-drain c	liode					
I <sub>S</sub>	source current	T <sub>amb</sub> = 25 °C	[1]	-	1.9	А

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.

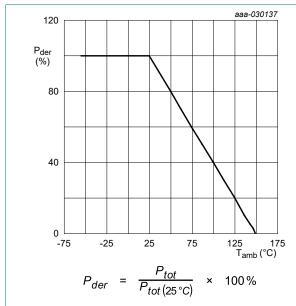


Fig. 1. Normalized total power dissipation as a function of ambient temperature

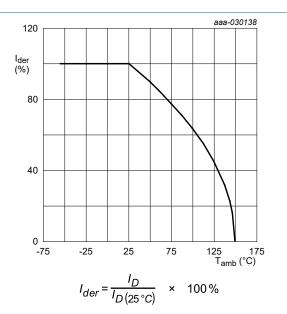


Fig. 2. Normalized continous drain current as a function of ambient temperature

### 40 V, N-channel Trench MOSFET

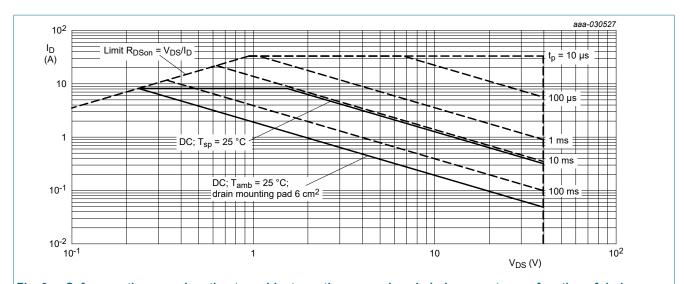


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

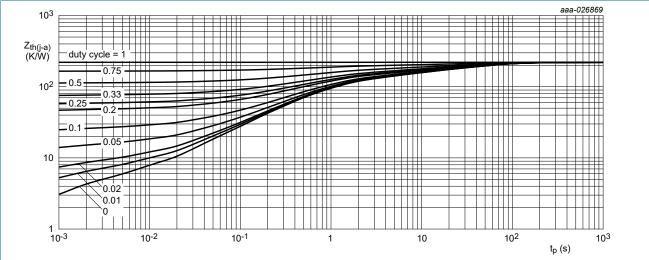
40 V, N-channel Trench MOSFET

### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

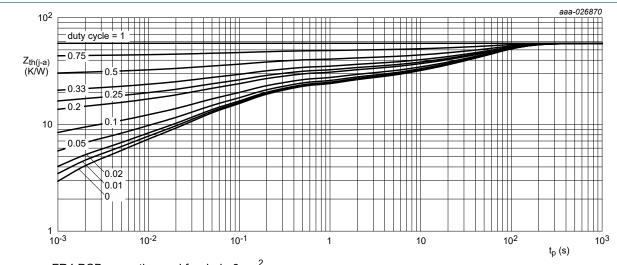
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
ui(j-a)	thermal resistance from	in free air	[1]	-	223	256	K/W
	junction to ambient		[2]	-	57	66	K/W
		in free air; t ≤ 5 s	[2]	-	29	33	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	6	10	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.



FR4 PCB, standard footprint

Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for drain 6 cm<sup>2</sup>

Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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## 10. Characteristics

#### **Table 7. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	40	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	0.4	0.65	0.9	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 40 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	1	μΑ
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = -8 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-100	nA
		V <sub>GS</sub> = 8 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	100	nA
R <sub>DSon</sub>	drain-source on-state	$V_{GS} = 4.5 \text{ V}; I_D = 8.1 \text{ A}; T_j = 25 ^{\circ}\text{C}$	-	15	18	mΩ
resistance	resistance	V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 8.1 A; T <sub>j</sub> = 150 °C	-	24	29	mΩ
		$V_{GS} = 2.5 \text{ V}; I_D = 7.3 \text{ A}; T_j = 25 ^{\circ}\text{C}$	-	17	22	mΩ
		V <sub>GS</sub> = 1.8 V; I <sub>D</sub> = 3 A; T <sub>j</sub> = 25 °C	-	23	32	mΩ
		V <sub>GS</sub> = 1.5 V; I <sub>D</sub> = 0.5 A; T <sub>j</sub> = 25 °C	-	40	100	mΩ
g <sub>fs</sub>	forward transconductance	$V_{DS} = 10 \text{ V}; I_D = 8.3 \text{ A}; T_j = 25 \text{ °C}$	-	22	-	S
$R_{G}$	gate resistance	f = 1 MHz	-	2.4	-	Ω
Dynamic ch	aracteristics					
Q <sub>G(tot)</sub>	total gate charge	$V_{DS} = 20 \text{ V}; I_D = 8.3 \text{ A}; V_{GS} = 4.5 \text{ V};$	-	19.4	28	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C	-	2.4	-	nC
$Q_{GD}$	gate-drain charge		-	5.6	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 20 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	1625	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	99	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	85	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 20 \text{ V}; I_D = 8.3 \text{ A}; V_{GS} = 4.5 \text{ V};$	-	5	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	8	-	ns
t <sub>d(off)</sub>	turn-off delay time	1	-	35	-	ns
t <sub>f</sub>	fall time	1	-	15	-	ns
Source-drai	in diode		1			
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = 1.9 A; V <sub>GS</sub> = 0 V; T <sub>i</sub> = 25 °C	-	0.7	1.2	V

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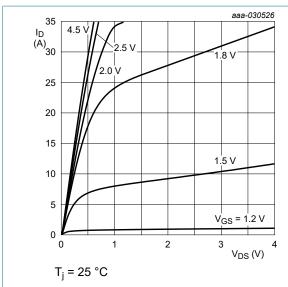


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

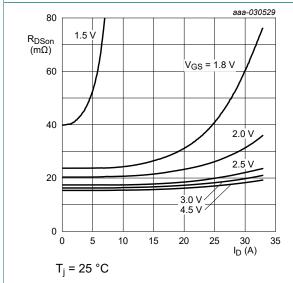


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

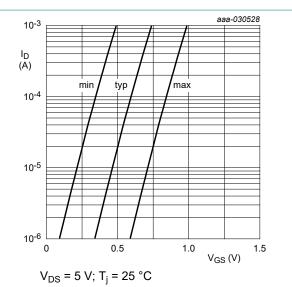


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

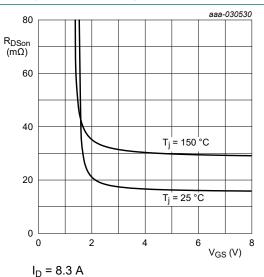


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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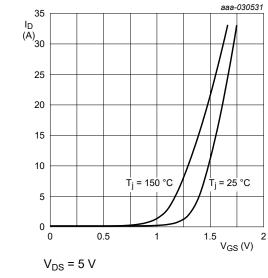


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

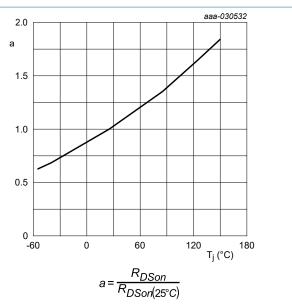


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

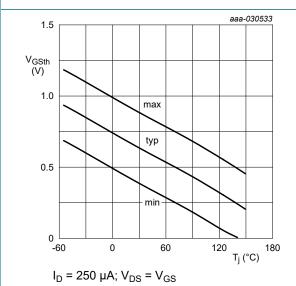


Fig. 12. Gate-source threshold voltage as a function of junction temperature

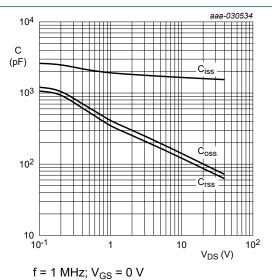


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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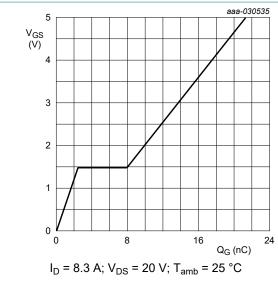


Fig. 14. Gate-source voltage as a function of gate charge; typical values

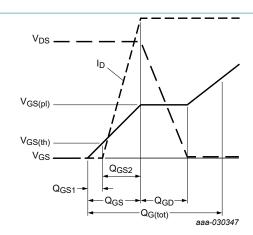


Fig. 15. Gate charge waveform definitions

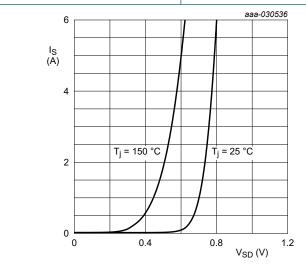
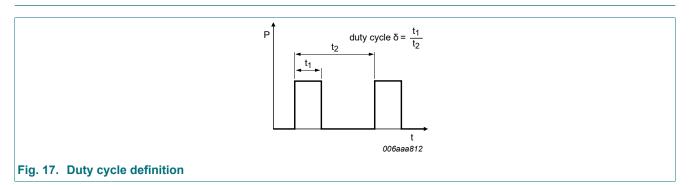


Fig. 16. Source current as a function of source-drain voltage; typical values

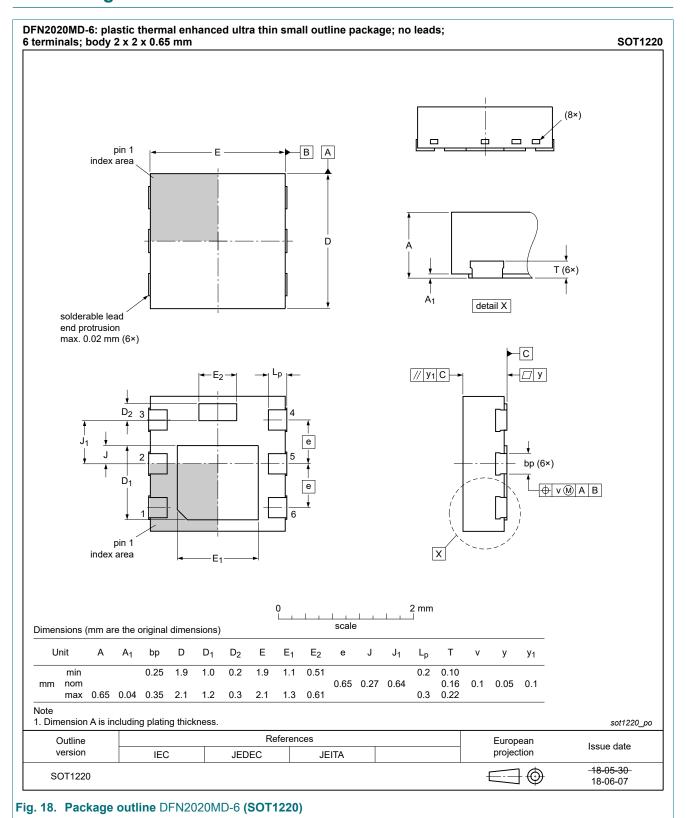
### 11. Test information

 $V_{GS} = 0 V$ 



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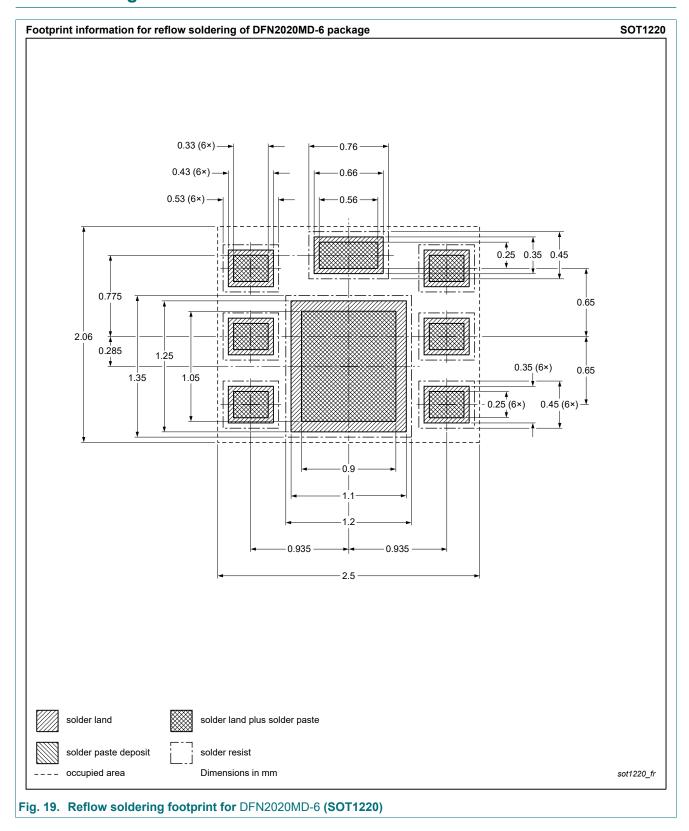
## 12. Package outline



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## 13. Soldering



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# 14. Revision history

### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMPB14XN v.1	20200311	Product data sheet	-	-

#### 40 V, N-channel Trench MOSFET

## 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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